

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

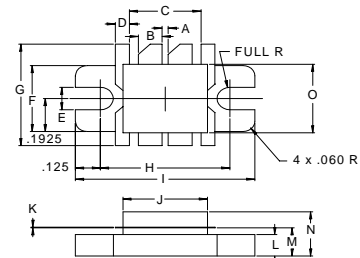
The **ASI TVV100** is Designed for Television Band III Applications up to 225 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 11$  dB at 100 W/225 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	16 A
$V_{CBO}$	65 V
$V_{CEO}$	33 V
$V_{EBO}$	3.5 V
$P_{DISS}$	150 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$\theta_{JC}$	$0.8^\circ C/W$

**PACKAGE STYLE .400 8L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.030 / 0.76
B	.115 / 2.92	.125 / 3.18
C		.360 / 9.14
D	.065 / 1.65	.075 / 1.91
E		.130 / 3.30
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

**ORDER CODE: ASI10662**
**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 50$ mA	65			V
$BV_{CER}$	$I_C = 50$ mA $R_{BE} = 15 \Omega$	60			V
$BV_{CEO}$	$I_C = 50$ mA	33			V
$BV_{EBO}$	$I_E = 5.0$ mA	3.5			V
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 500$ mA	20		150	---
$C_{OB}$	$V_{CB} = 28$ V $f = 1.0$ MHz	---	60	---	pF
$P_G$	$V_{CE} = 28$ V $I_C = 2 \times 100$ mA $f = 225$ MHz $P_{OUT} = 100$ W	11			dB